

COMPOSITIONS FOR CLEANING ORGANIC AND PLASMA ETCHED RESIDUES  
FOR SEMICONDUCTOR DEVICES

ABSTRACT OF THE DISCLOSURE

5 A composition for the stripping of photoresist and the cleaning of residues from substrates,  
and for silicon oxide etch, comprising from about 0.01 percent by weight to about 10  
percent by weight of one or more fluoride compounds, from about 10 percent by weight to  
about 95% by weight of a sulfoxide or sulfone solvent, and from about 20 percent by weight  
to about 50 percent by weight water. The composition may contain corrosion inhibitors,  
10 chelating agents, co-solvents, basic amine compounds, surfactants, acids and bases.

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